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CERTIFICATE OF TRANSMISSION

November 5, 2004

Atty Docket No. :	JCLA7737-R
Appl. No. :	10/015,414
Filing Date :	December, 12, 2001
Pages :	Cover + 2

BY FACSIMILE ONLY

Fax No. :	703-746-4000
Attention :	BOX ISSUE FEE Commissioner for Patents
From :	Jiawei Huang, Reg. No. 43,330
MESSAGE :	Enclosed herewith are: <input checked="" type="checkbox"/> Issue Fee Transmittal Sheet. <input checked="" type="checkbox"/> Comments on Statement of Reasons for Allowance.

Sir:

I hereby certify that this correspondence is being facsimile transmitted to the Patent and Trademark Office on November 5, 2004 at the above indicated fax number.

Sign by: Michelle Chang
 Michelle Chang

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PATENT
Docket No. JCLA7737-R
US App. No. 10/015,414

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: : TSO-HUNG FAN et al.)
Application No.: : 10/015,414)
Filed: : December 12, 2001)
For: : METHOD FOR PROGRAMMING AND)
ERASING NON-VOLATILE MEMORY)
WITH NITRIDE TUNNELING LAYER)

COMMENTS ON STATEMENT OF REASONS FOR ALLOWANCE

Mail Stop Issue Fee
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

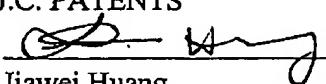
Dear Sir:

Applicant respectfully submits the following comments on Examiner's statement of reasons for allowance.

In the Notice of Allowability mailed September 20, 2004, the Examiner stated that "the prior art did not teach the method above further applied in non-volatile memory cell being provided with a nitride tunneling layer disposed on the substrate, without a dielectric layer therebetween, ...". Applicant would like to point out that, in the allowed claims 5-7 and 9-11, there is no such limitation as "without a dielectric layer therebetween" (between the substrate and the nitride tunneling layer) being recited.

Date: 11/5/2004

Respectively submitted
J.C. PATENTS


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